CLAIMS:

1. A resist composition comprising a fluorochemical surfactant which functions to reduce the contact angle at the interface between the surface of the resist composition coated onto a substrate and water or an aqueous base developer as the amount of the fluorochemical surfactant increases.

2. The resist composition of claim 1 wherein said fluorochemical surfactant is of the following general formula (1):

$$Rf-[(CH_2)_aO]_m-CH_2CHR^1CH_2O-(CH_2CHR^2O)_n-CH_2CHR^1CH_2-[O(CH_2)_a]_m-Rf' \quad (1)$$

wherein R^1 is hydrogen, a hydroxyl group, a straight, branched or cyclic alkoxy group of 1 to 6 carbon atoms, or an alkylcarbonyloxy group whose alkyl moiety has 1 to 6 carbon atoms, R^2 is hydrogen or a straight, branched or cyclic alkyl group of 1 to 6 carbon atoms, a is a positive integer of 0 to 6, m is equal to 0 or 1, and n is a positive integer of 1 to 40, each of Rf and Rf', which may be the same or different, is a straight, branched or cyclic fluoroalkyl group having 1 to 12 carbon atoms, in which all groups attached to its carbon atoms are fluorine atoms or some are fluorine atoms and the remainder are hydrogen atoms.

3. The resist composition of claim 1 which is of chemical amplification type and to be exposed to high-energy radiation having a wavelength of 500 nm or less, x-rays or electron beams.

4. A method for forming a resist pattern comprising the steps of:

(i) coating a resist composition according to claim 3 onto a substrate,

(ii) heat treating the coated film and then exposing it to high-energy radiation having a wavelength of 500 nm or less, x-rays or electron beams through a photo mask, and

(iii) optionally heat treating the exposed film and developing it with a developer.